

Toward Waste Heat Recovery Using Nanostructured Thermoelectrics

Sanjiv Sinha

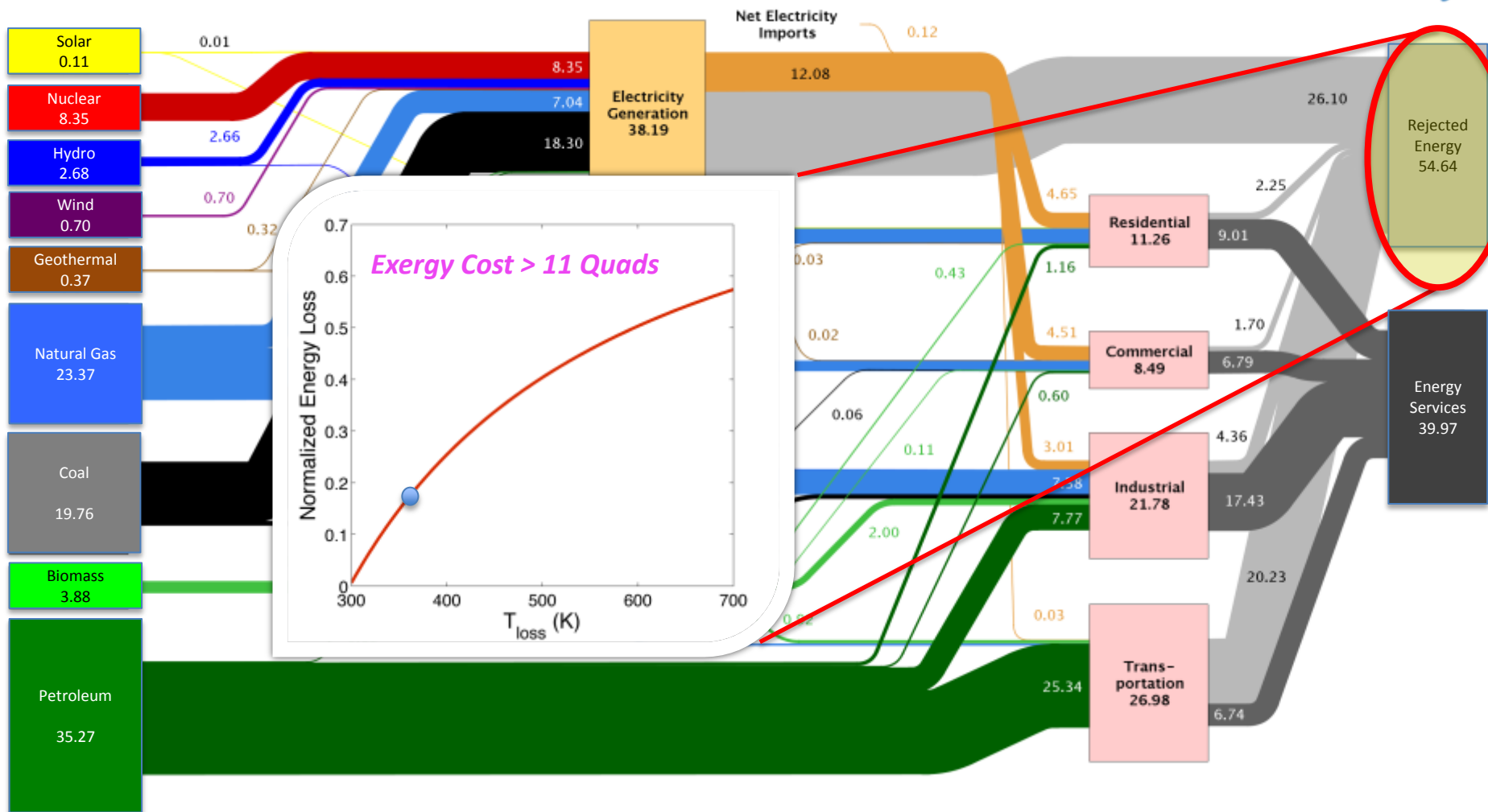
Mechanical Science & Engineering
University of Illinois at Urbana-Champaign



Potential for Waste Heat Harvesting

Estimated U.S. Energy Use in 2009: ~94.6 Quads

Lawrence Livermore
National Laboratory



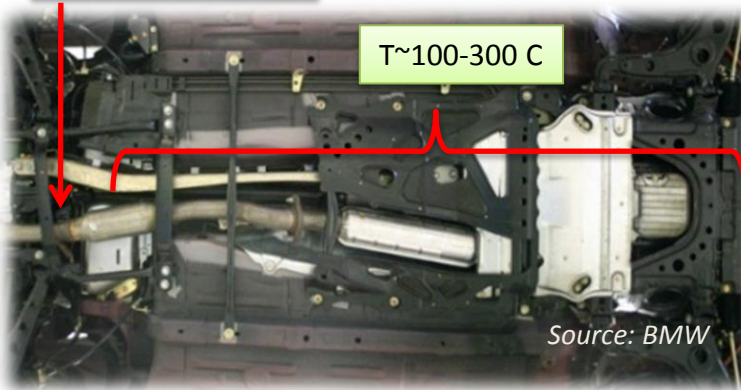
~ 57% of energy consumed in the US rejected as heat

Sources of Low Quality Waste Heat



$T_{\text{water}} \sim 33 \text{ C}$
 $T_{\text{flue}} \geq 100 \text{ C}$ ($\eta_{\text{furnace}} \sim 90\%$)

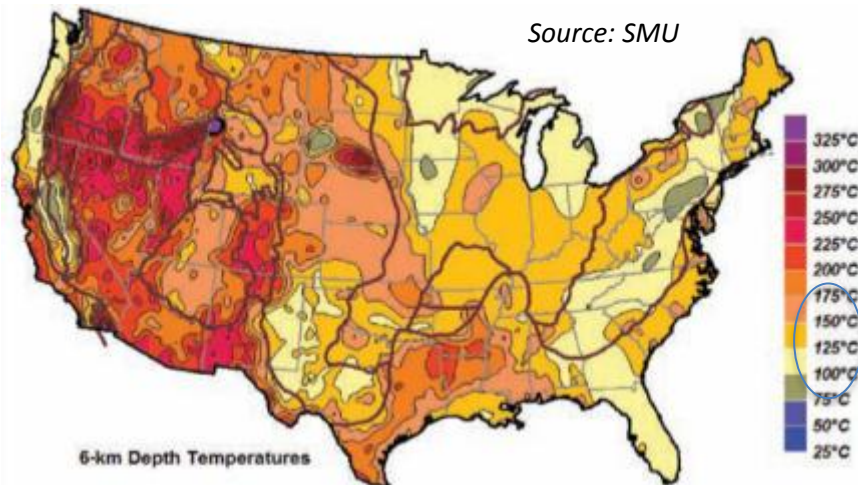
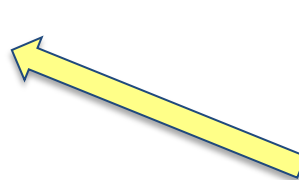
$T_{\text{exhaust}} \sim 400\text{-}600 \text{ C}$



$T \sim 100\text{-}300 \text{ C}$

Source: BMW

$T_{\text{IN}} \sim 27 \text{ C}$ (ASHRAE)
 $\delta T \sim 50 - 120 \text{ C}$ (HD, State of art at Intel)



- $\eta_{\text{CARNOT}} (T_H=100\text{C}) \sim 20\%$
- Difficult to extract work
- Fluid machines infeasible
- Transcritical CO_2 , organic Rankine, Kalina are expensive
- Thermoelectrics?

Thermoelectrics



Thomas Johann
Seebeck (1770-1831)

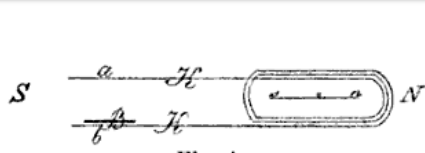


Fig. 1.

1821-22

Seebeck, T.J., "Magnetische polarisation der metalle und erze durch temperaturdifferenz", Verlag von Willhelm Engelmann, Leipzig, Germany (1895)

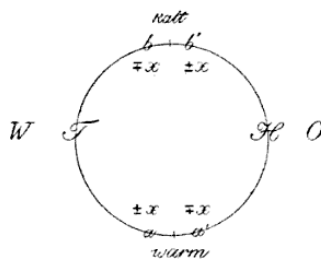
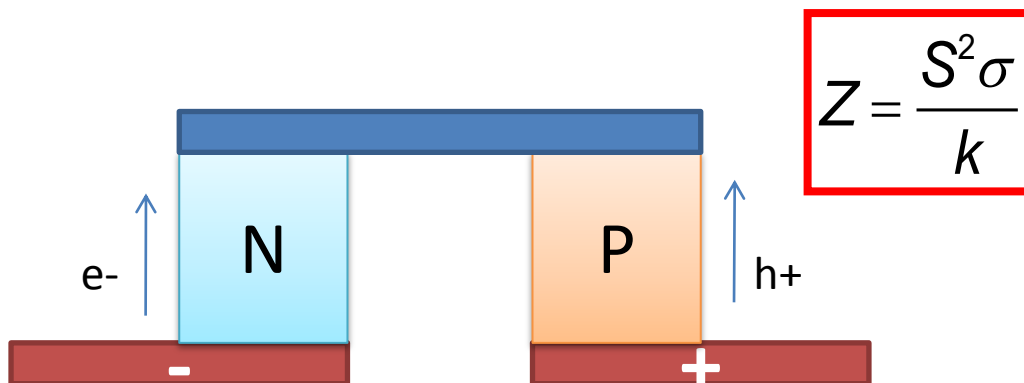


Fig. 26.

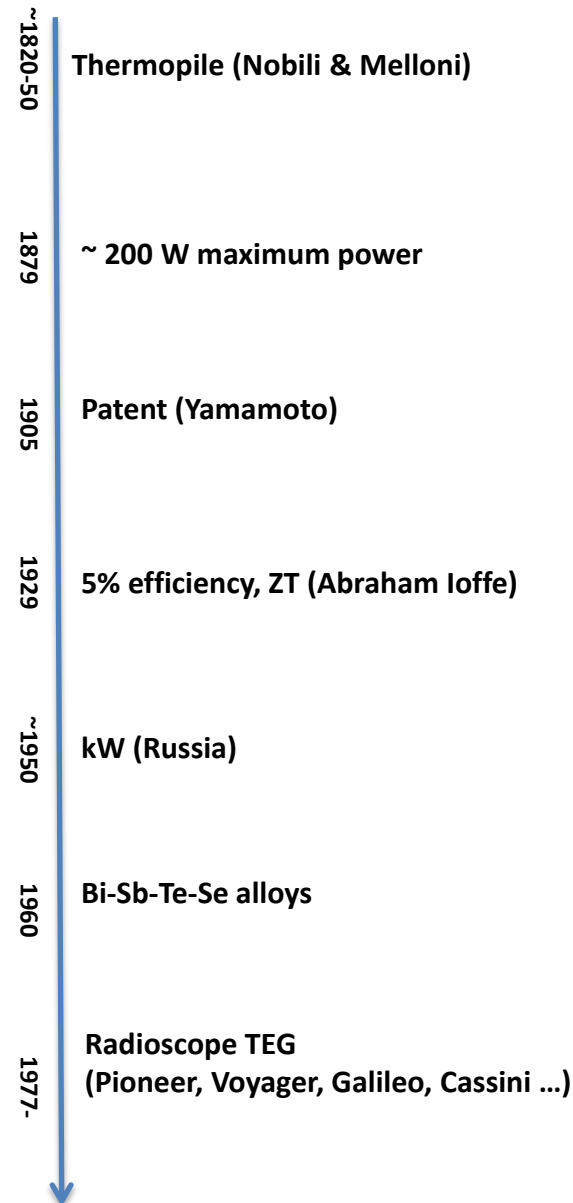
$$V_{SEEBECK} = \int_C^H \nabla \phi \, d\vec{r} = - \int_C^H S(T) \nabla T \, d\vec{r} = -S \Delta T$$

$$S \sim k/e @ 10^{-4} \, V/K$$



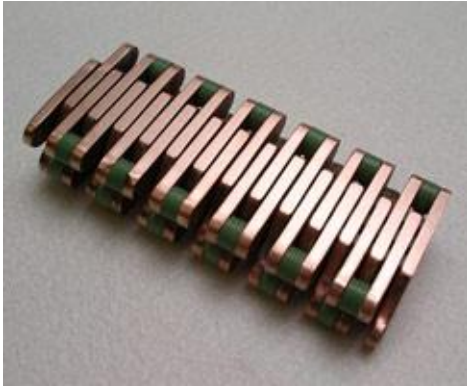
π -leg p - n Thermoelectric Junction

Thermoelectric Generators



Thermoelectrics Applications

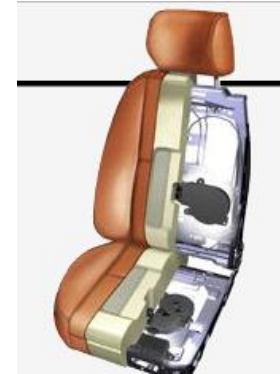
BSST



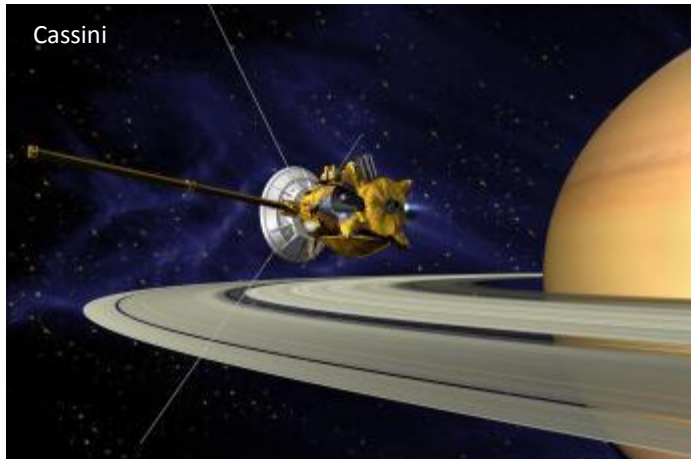
Refrigeration



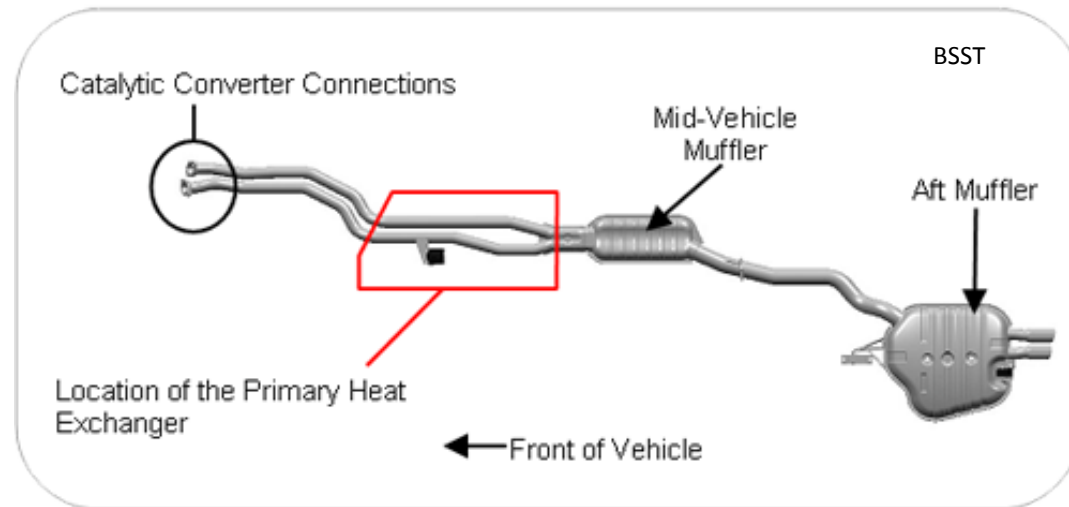
Amerigon



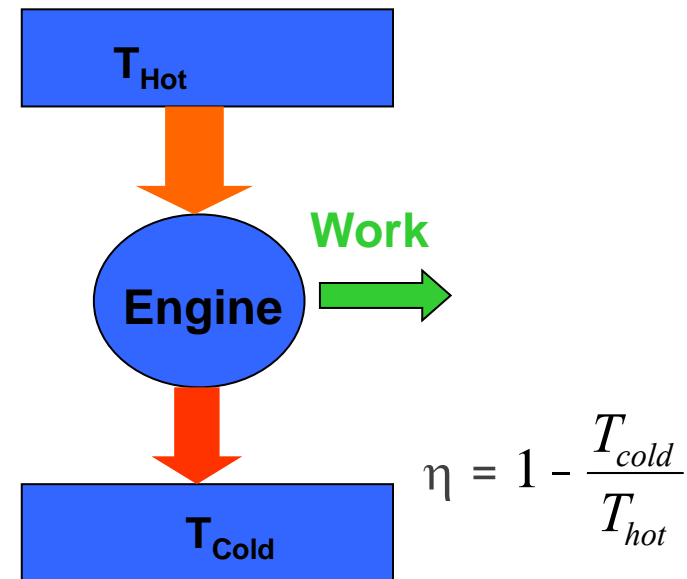
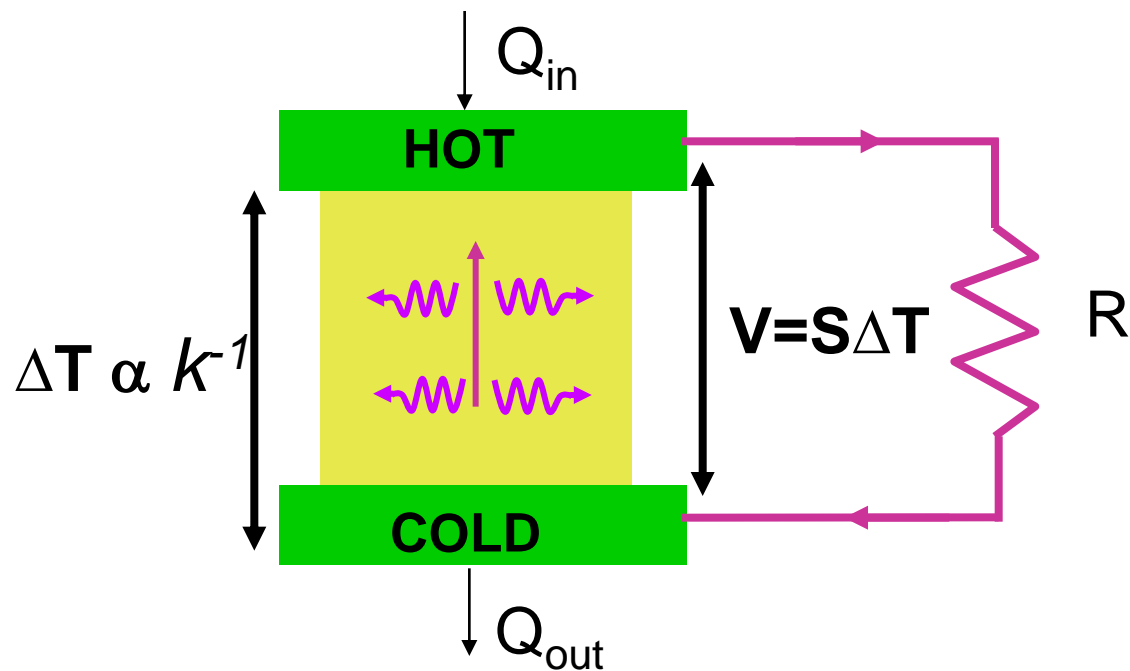
Power Generation



Waste Heat Recovery

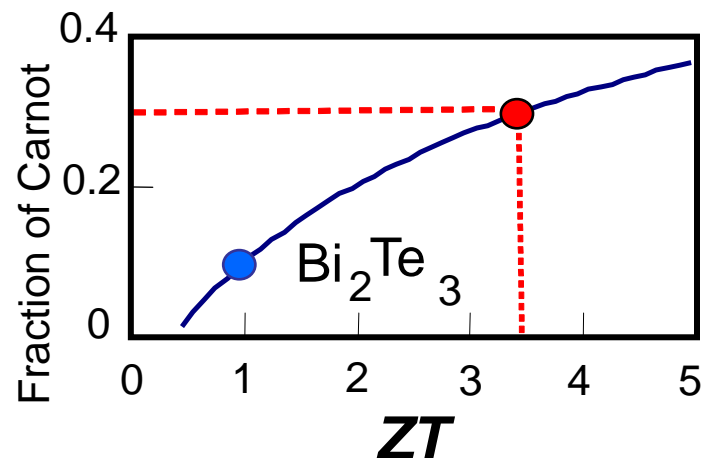


The Thermoelectric Heat Engine



$$h = h_{\text{CARNOT}} \frac{\sqrt{1 + ZT} - 1}{\sqrt{1 + ZT} + \frac{T_C}{T_H}}$$

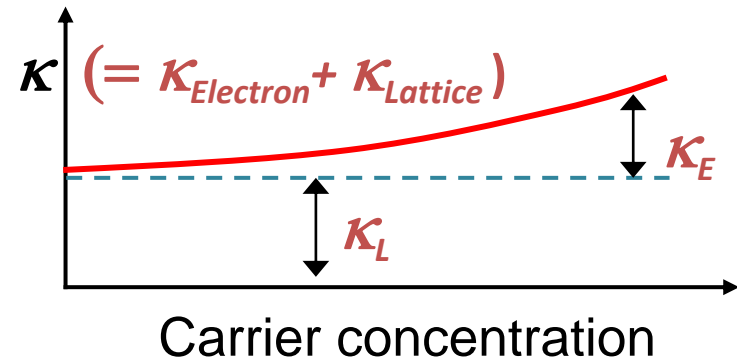
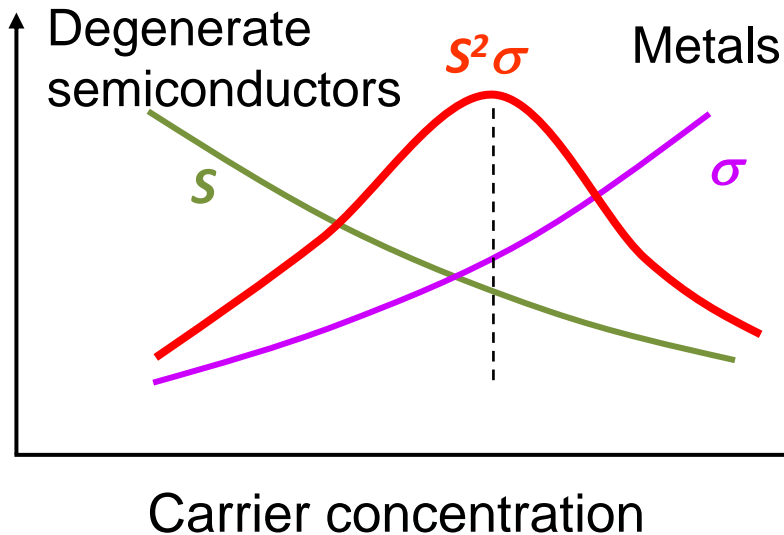
$$ZT = \frac{S^2 \sigma T}{k}$$



◎ The Z Conundrum

$$Z = \frac{S^2 \sigma}{k}$$

- Microscopic linkage between S , σ and k



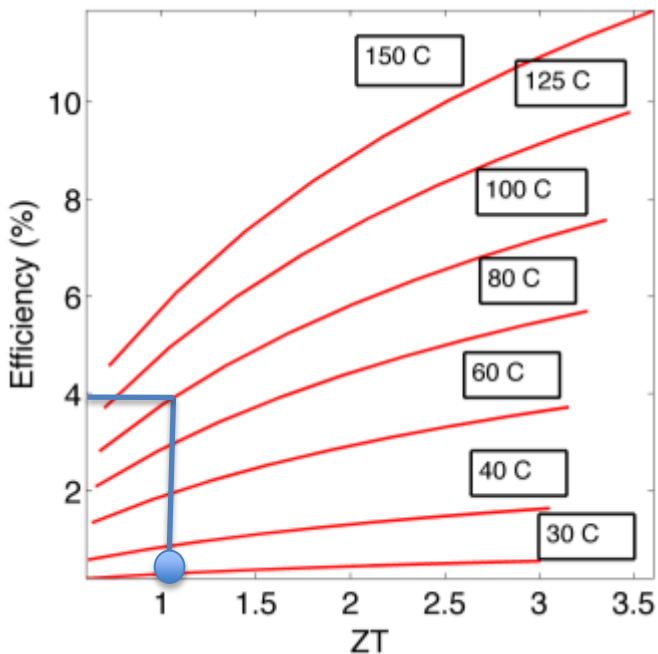
$$\frac{k}{S} = LT$$

Wiedemann Franz Law

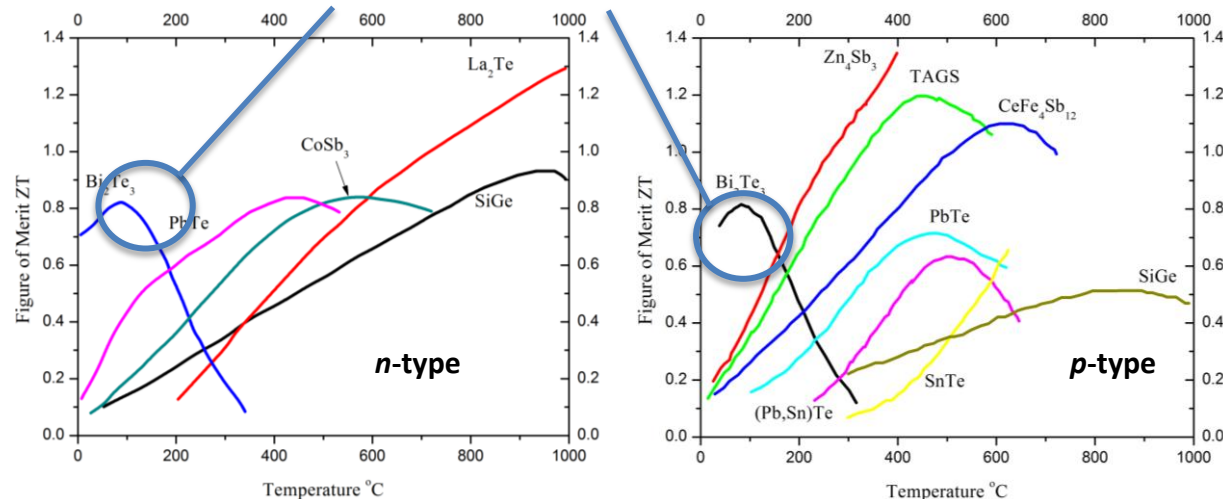


Conversion Efficiency

$$h = h_{\text{CARNOT}} = \frac{\sqrt{1 + ZT} - 1}{\sqrt{1 + ZT} + \frac{T_C}{T_H}}$$



Bi₂Te₃ alloys have ZT ~ 1 at 300 K



Scalability Issues:

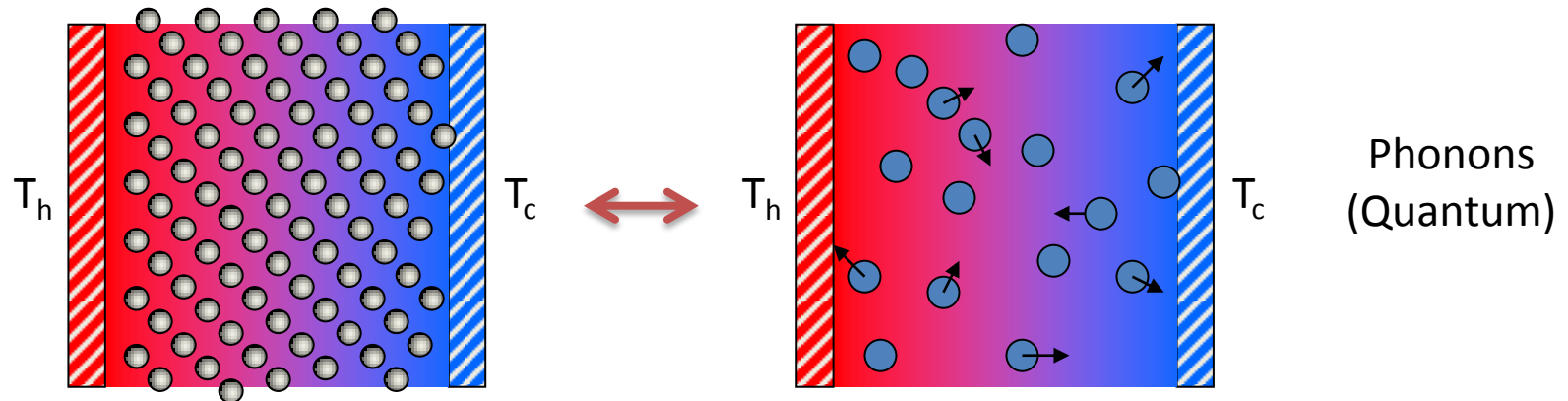
- Low abundance
- ~15x expensive as Si

What about silicon?
k ~ 150 W/mK (300 K)

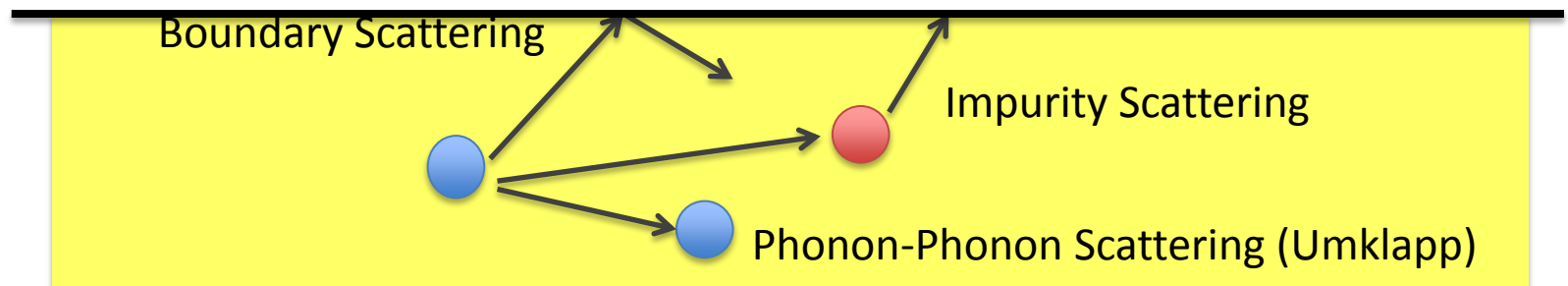
➔ *Bulk ZT ~ 0.01*

Thermal Conductivity

- Lattice vibrations conduct heat in Si



- From Kinetic theory, $k \sim C v \Lambda$
- Λ limited by different scattering processes

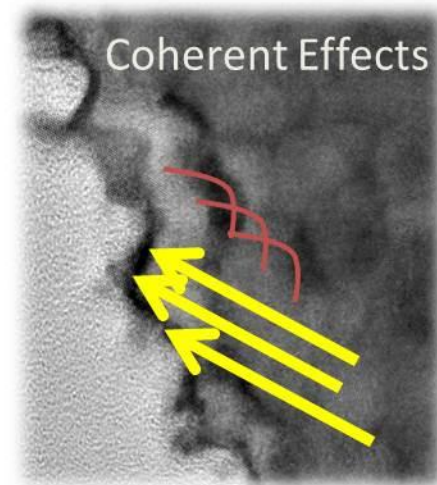
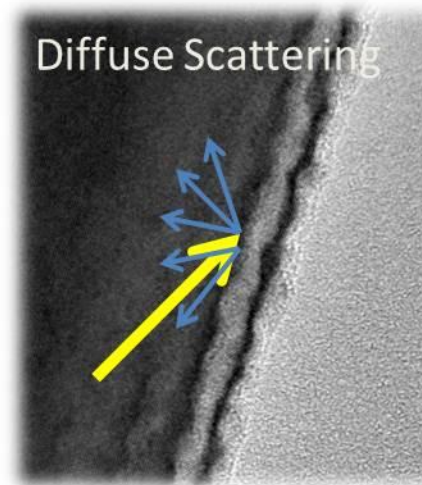
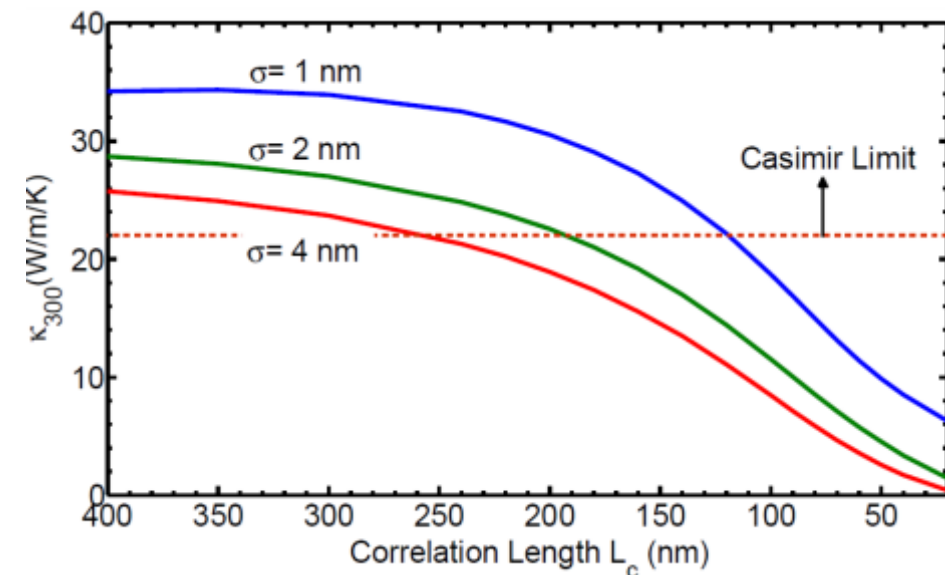
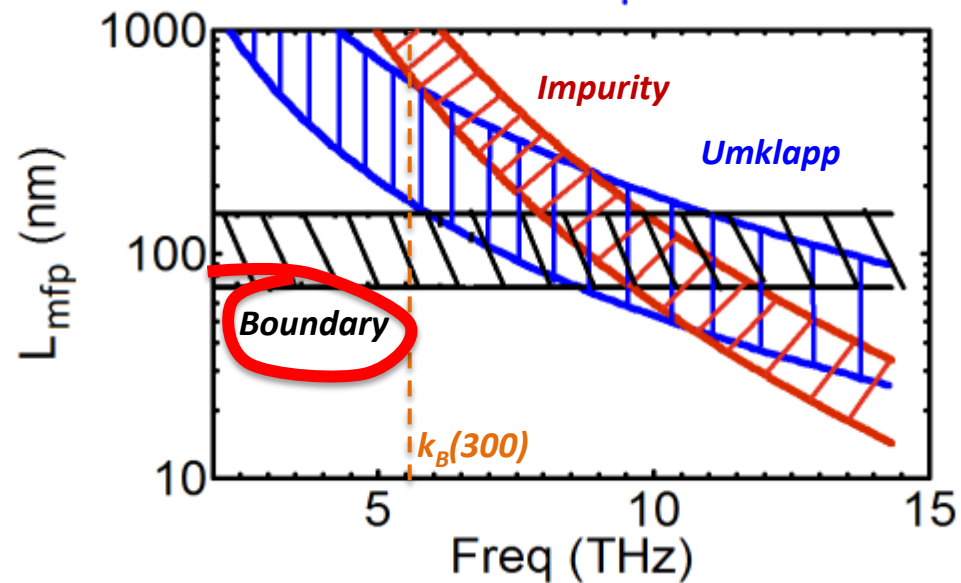


○ Silicon Thermal Conductivity

$$\Lambda_{\text{PHONON}} \sim 100\text{-}300 \text{ nm}$$

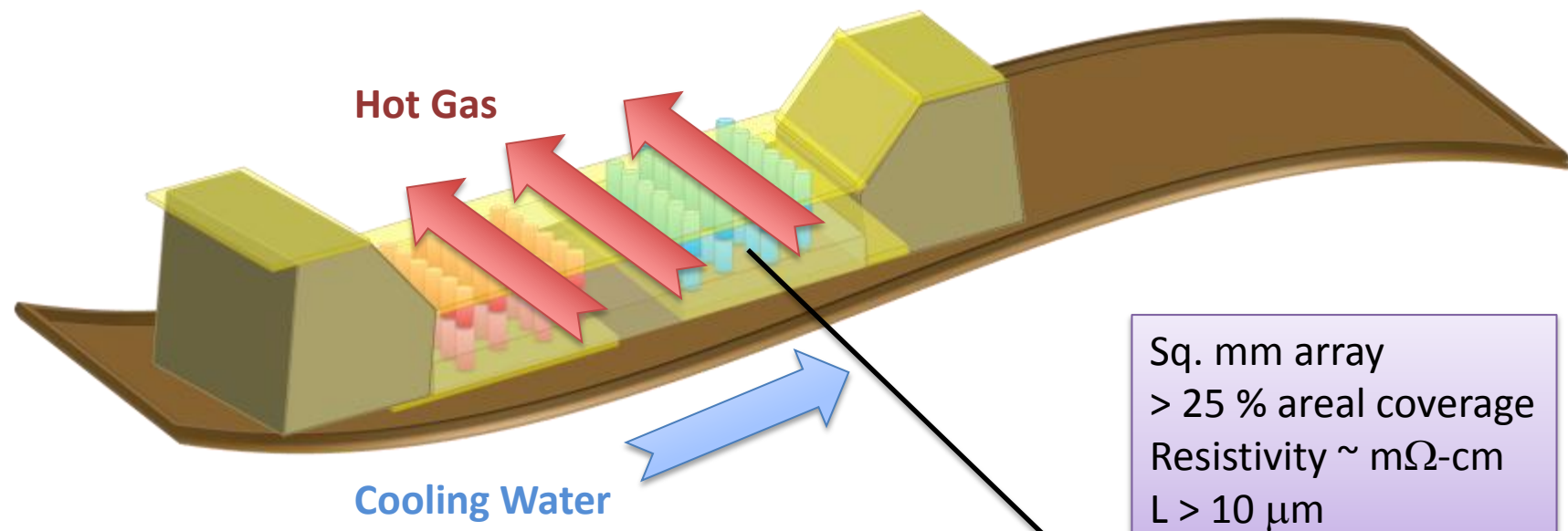
Boundary scattering dominates in 100 nm Si

Phonon boundary scattering is frequency dependent and tunable through roughness

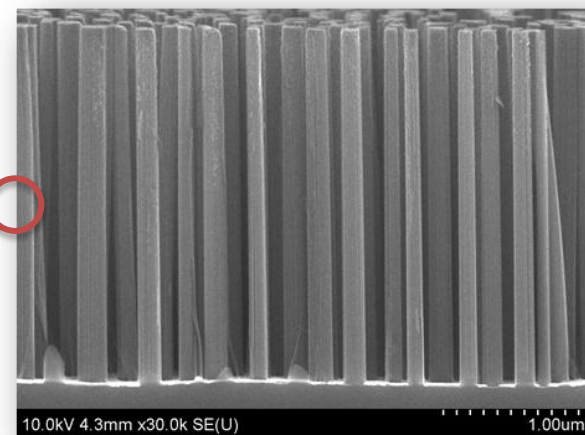
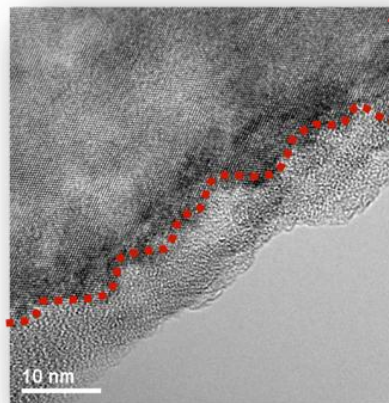


Smooth vs Rough

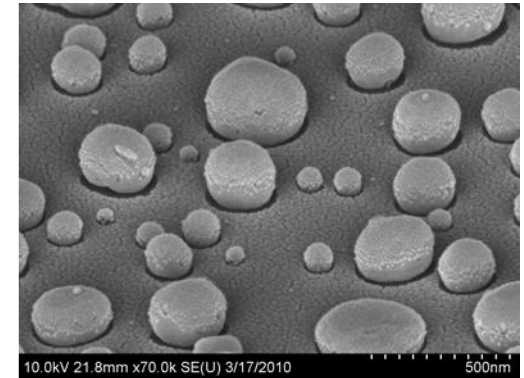
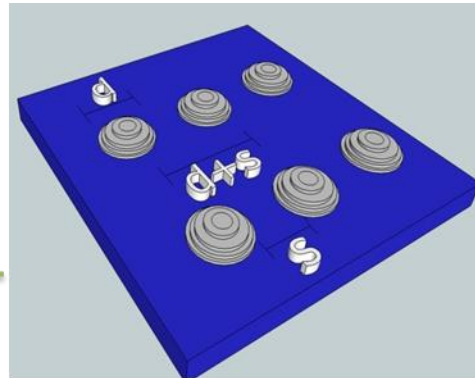
UIUC Silicon TE Device Concept



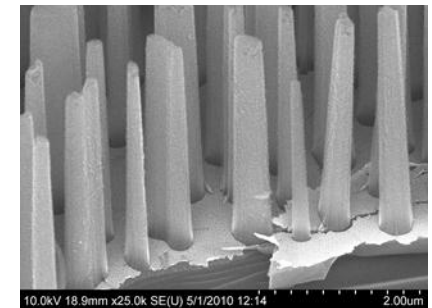
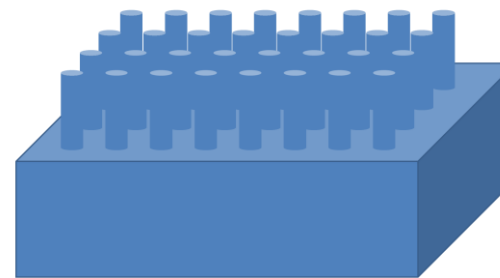
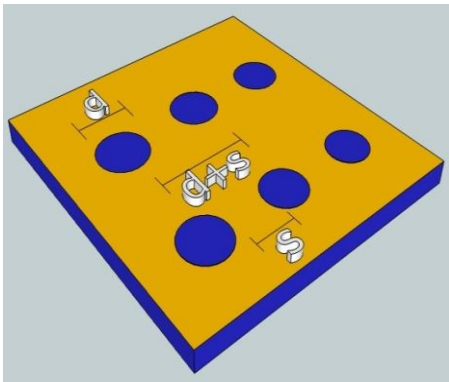
Rms roughness $> 2\text{nm}$
Corr. Length $< 100 \text{ nm}$
Dia $< 100 \text{ nm}$



Wire Array Fabrication



Thermal Dewetting



MAC-Etch

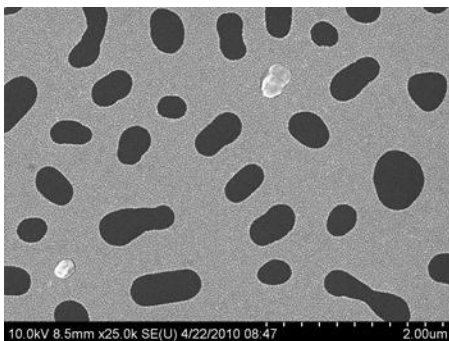
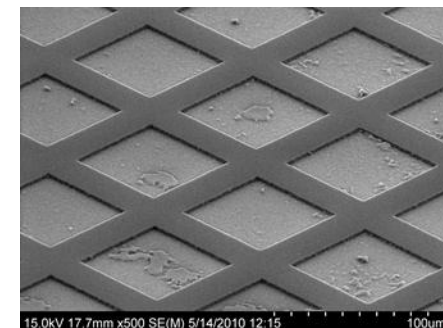
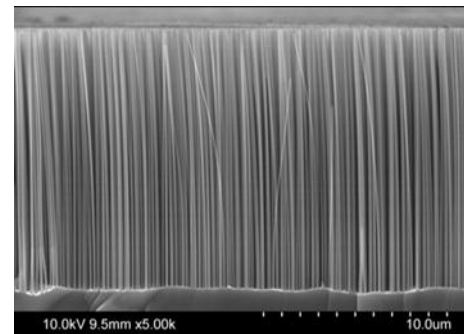
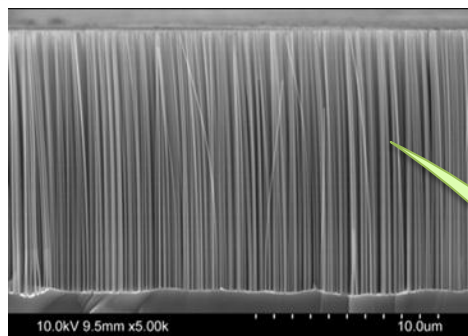


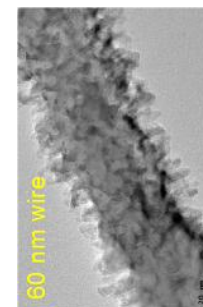
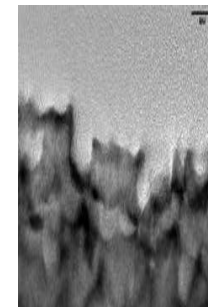
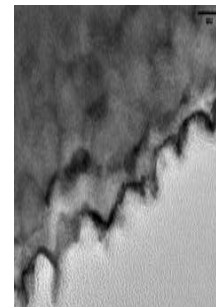
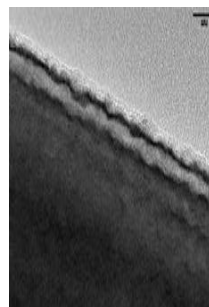
Image Reversal via Lift-Off



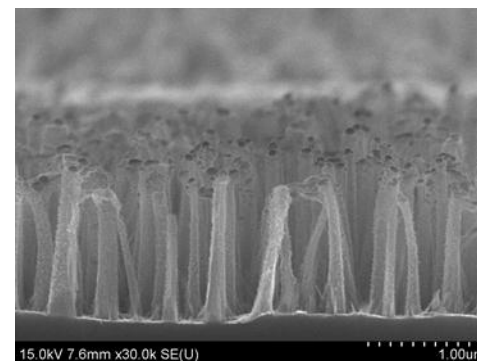
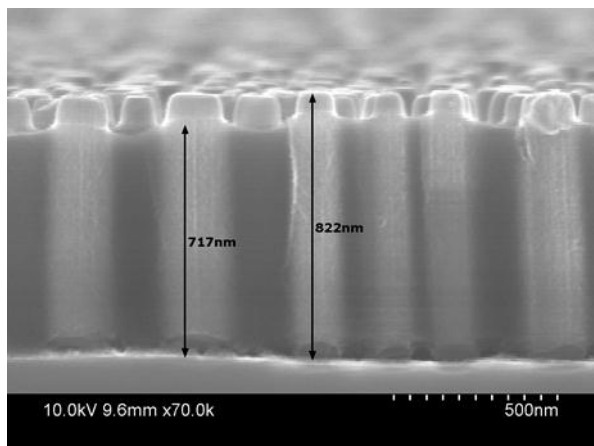
Device Formation



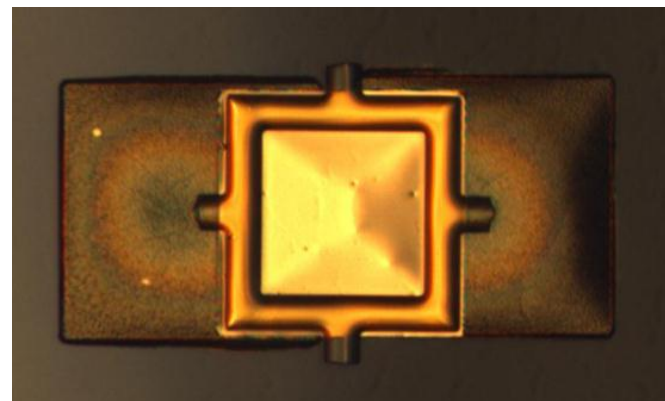
Controlled
Roughness
Enhancement



SOG/Poly Fill &
Contact Formation



Transfer Printing (*n*- and *p*-type)



HRTEM Roughness Characterization



Roughened wire still crystalline

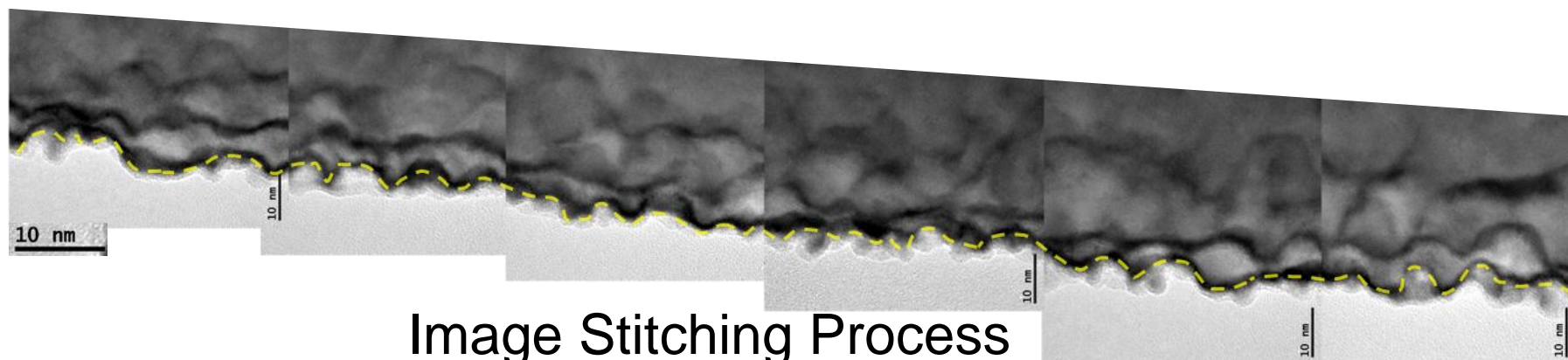
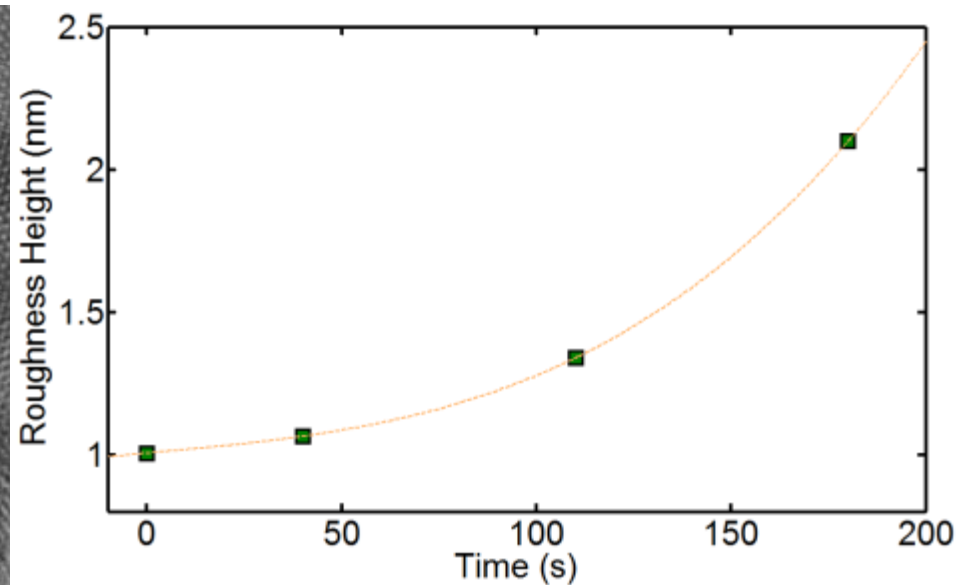
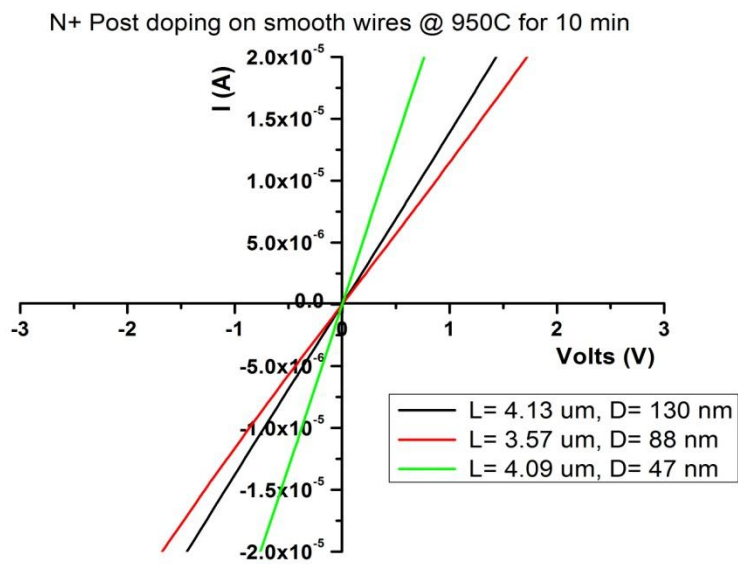
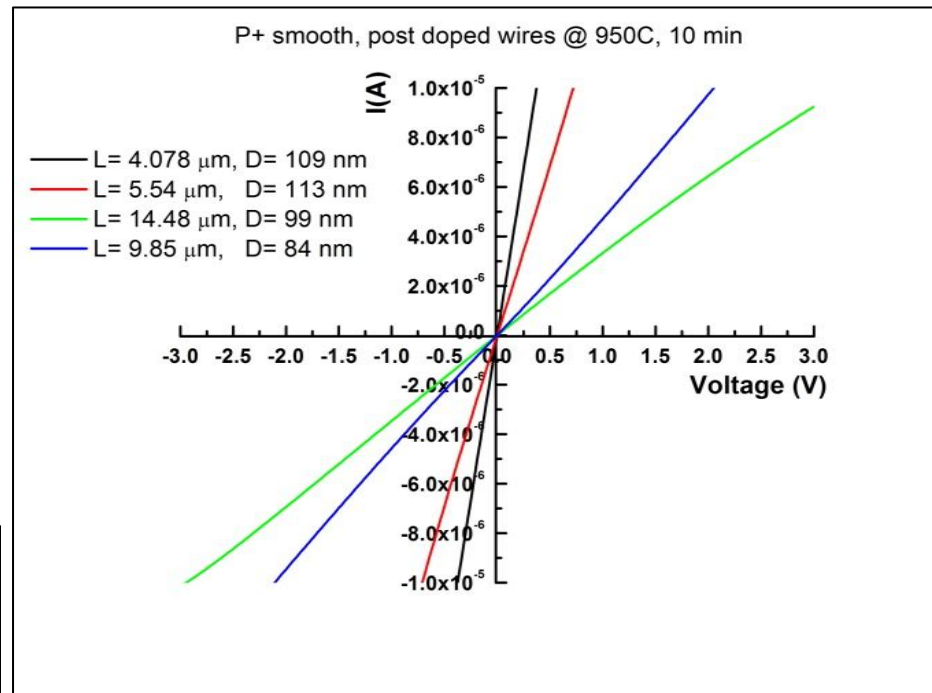
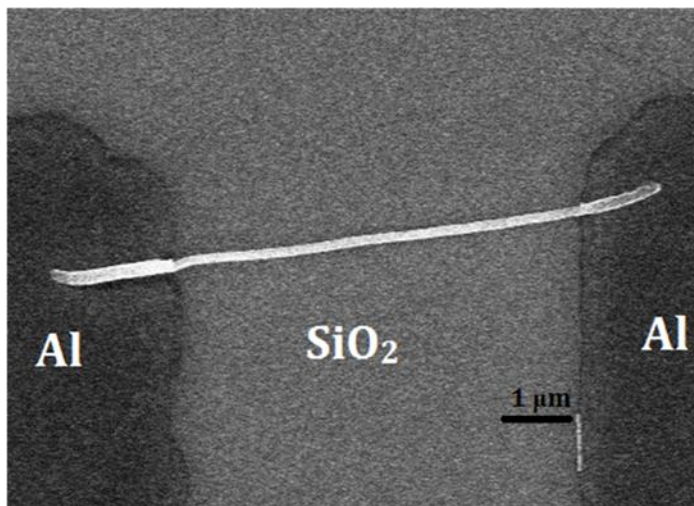


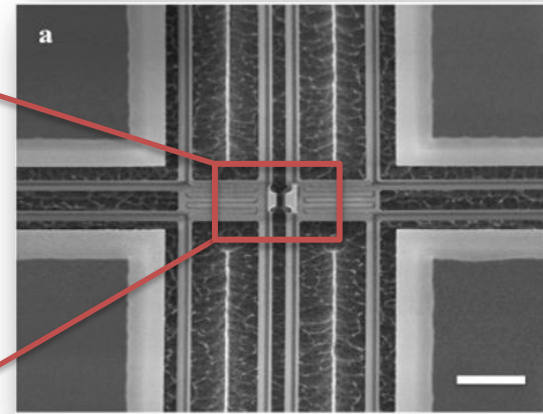
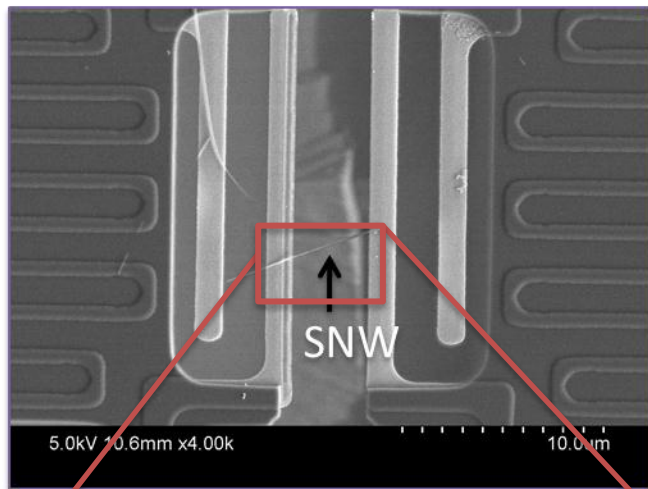
Image Stitching Process

Electrical Conductivity Measurements

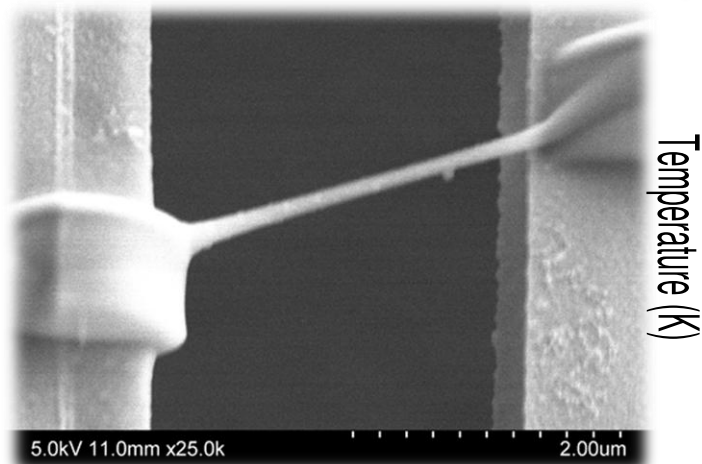
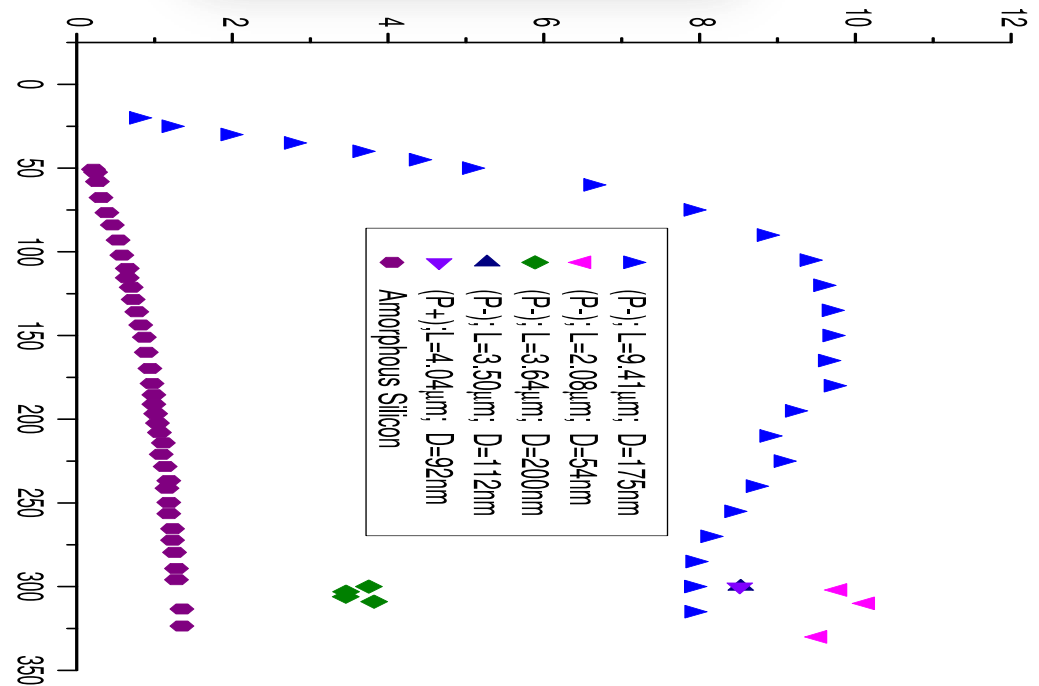


ρ can be reduced to $\sim 1 \text{ m}\Omega\text{-cm}$ via controlled doping

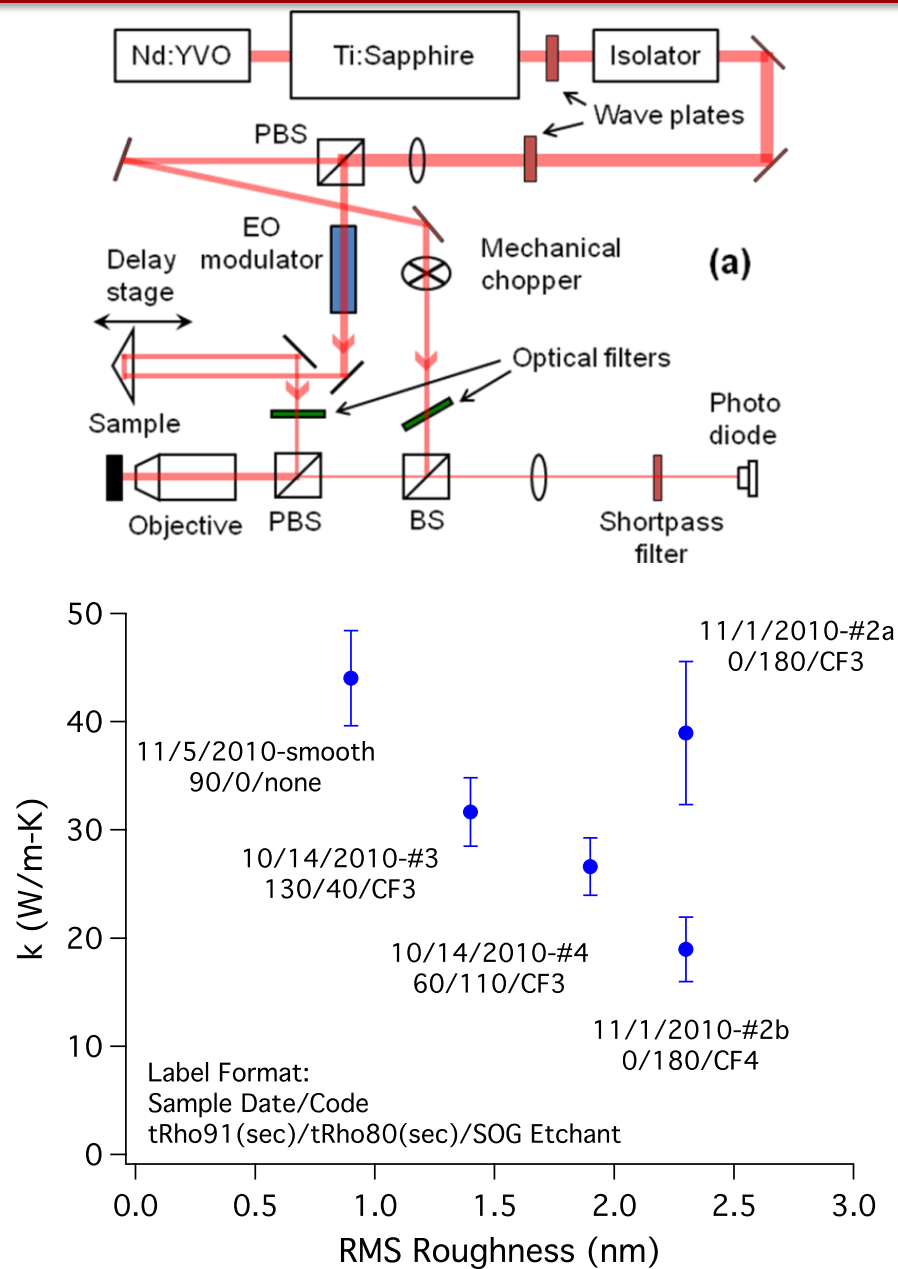
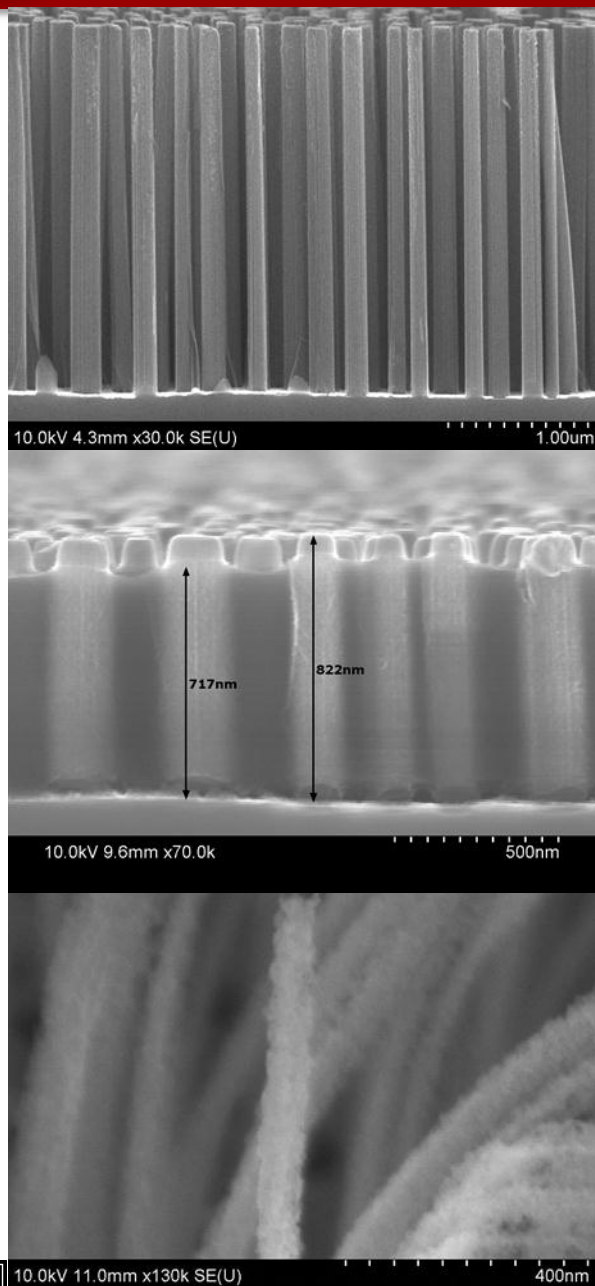
Single Wire Thermal Measurements



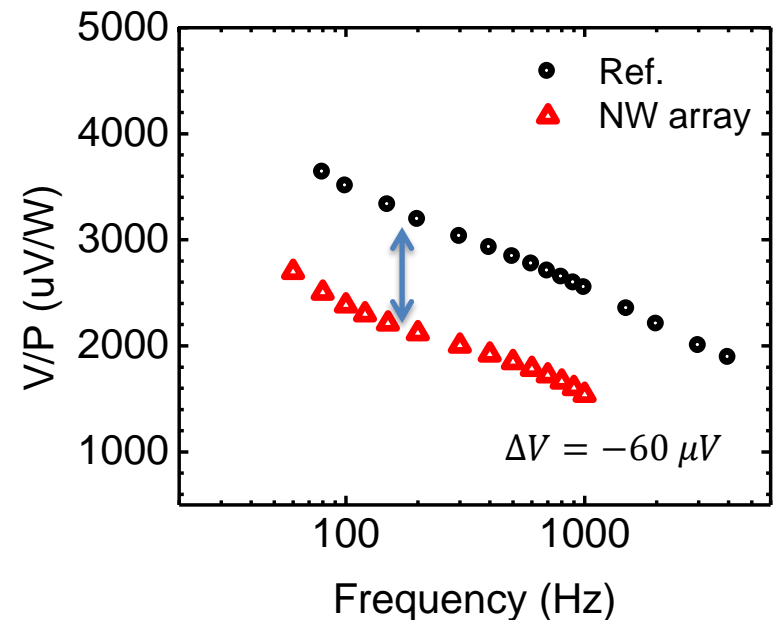
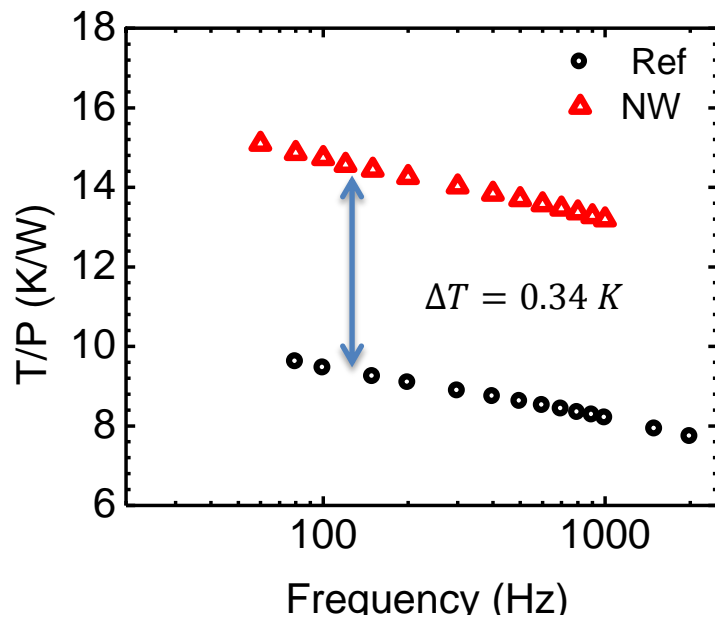
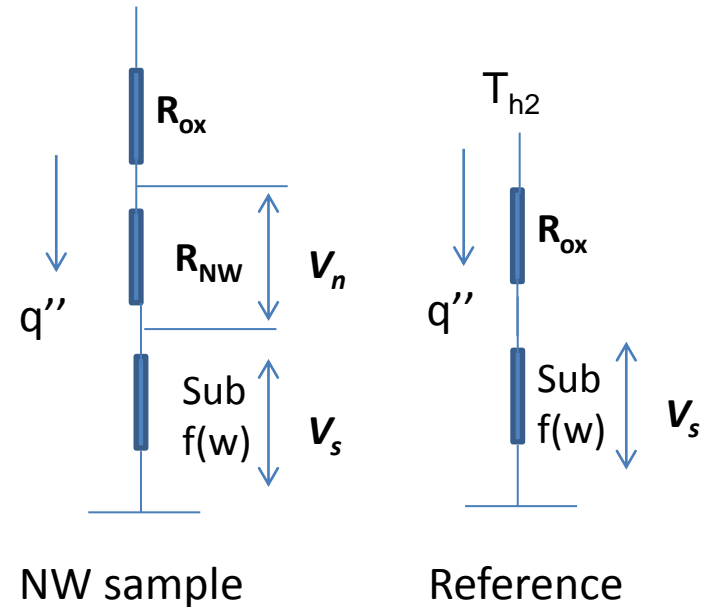
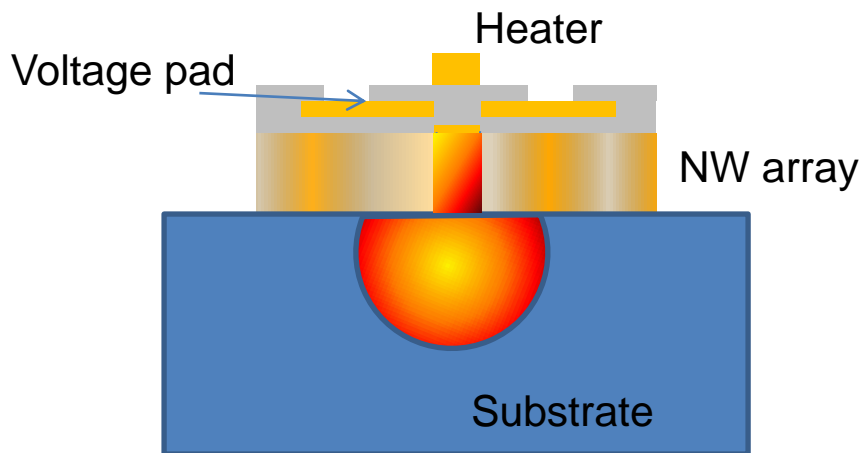
Thermal Conductivity (W/mK)



Thermal Conductivity of Wire Arrays



Array Seebeck and Thermal Measurements



Summary and Outlook

- Silicon thermoelectrics potentially enables unprecedented cost-effective waste heat recovery
- Ongoing work at UIUC seeks to fabricate the first truly nanostructured silicon thermoelectric device
- Preliminary characterization work shows promising trend and focus is now on device engineering



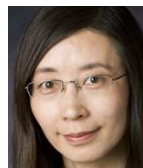
Cahill



Fang



Ferreira



Li



Rogers



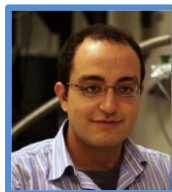
Sinha



Keng



Bruno



Marc



Jun



Seok



Numair



Dongwook



Myunghoon



Krishna



Jyothi

Joe Feser

Jae Cheol

Jae Ha

Chen

Jun-Hwan

